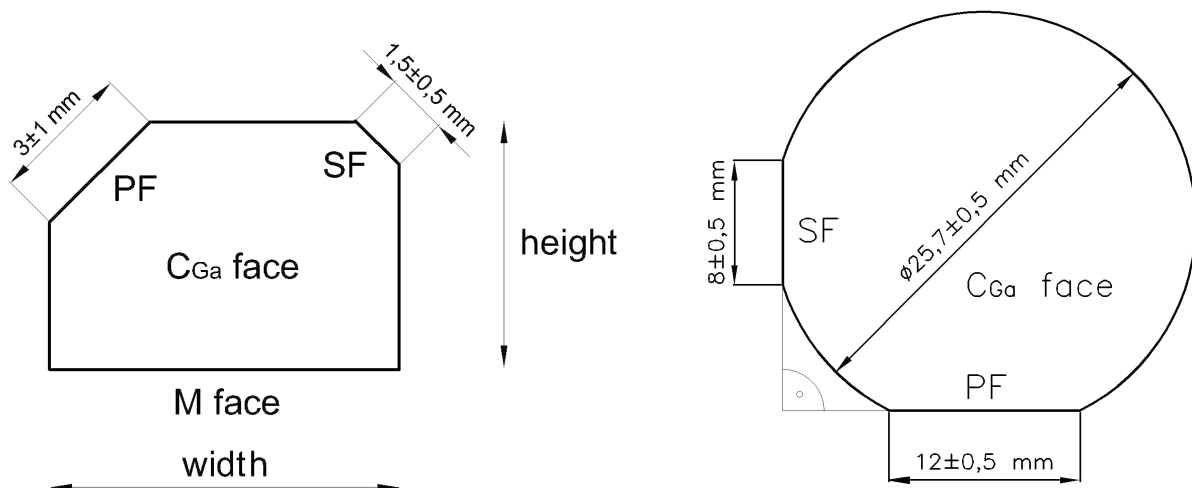


Ultra High Resistivity Semi-Insulating Ammono-GaN substrates

Features	Units	ORIENTATION
		c-plane
Carrier concentration	cm ⁻³	-
Resistivity	Ω·cm	10 ⁹ - 10 ¹²
Mobility	cm ² /V·s	-
Thickness	μm	≥ 300
Total thickness variation (TTV)	μm	< 40
Bow	μm	≤ 10
FWHM of X-ray rocking curve, epi-ready surface at 100 μm x 100 μm slit)	arcsec	~ 20
Dislocation density	cm ⁻²	~ 5·10 ⁴
Misorientation	deg	On demand
Surface finishing		As cut / ground Roughly polished Optically polished (RMS < 3 nm) Epi-ready (RMS < 0.5 nm)
Available sizes		10 x 10 mm ² , 1", 1.5"
Packaging		Separate single wafer container
Special Order Option		Please, contact Sales Department



Rectangular and 1" round substrates

Note: The information given above may be subject to change at any time without notice. This leaflet is not an offer within the meaning of sales or commercial law. The Ammono GaN substrates are offered for sale under Ammono's General Terms and Conditions.